

# Enhancement Mode N-Channel Power MOSFET

## Features

- ◆ Low  $R_{DS(on)}$  & FOM
- ◆ Extremely low switching loss
- ◆ Excellent stability and uniformity
- ◆ Easy to drive

## Applications

- ◆ Lighting
- ◆ Hard switching PWM
- ◆ Server power supply
- ◆ Charger

## ■ General Description

OSG90R1K2xF use advanced GreenMOSTM technology to provide low  $R_{DS(ON)}$ , low gate charge, fast switching and excellent avalanche characteristics. This device is suitable for active power factor correction and switching mode power supply applications.

◆ $V_{DS, min@Tjmax}$	960 V
◆ $I_{D, pulse}$	15 A
◆ $R_{DS(ON), max @ V_{GS}=10 V}$	1.2 $\Omega$
◆ $Q_g$	12.5 nC

## ■ Schematic and Package Information



## ■ Absolute Maximum Ratings at $T_j=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Value	Unit
Drain source voltage	$V_{DS}$	900	V
Gate source voltage	$V_{GS}$	$\pm 30$	V
Continuous drain current <sup>1)</sup> , $T_C=25^\circ\text{C}$	$I_D$	5	A
Continuous drain current <sup>1)</sup> , $T_C=100^\circ\text{C}$		3.2	
Pulsed drain current <sup>2)</sup> , $T_C=25^\circ\text{C}$	$I_{D, pulse}$	15	A
Power dissipation <sup>3)</sup> , $T_C=25^\circ\text{C}$	$P_D$	83	W
Single pulsed avalanche energy <sup>5)</sup>	$E_{AS}$	211	mJ
MOSFET dv/dt ruggedness, $V_{DS}=0\dots 480\text{ V}$	dv/dt	50	V/ns
Reverse diode dv/dt, $V_{DS}=0\dots 480\text{ V}$ , $I_{SD}\leq I_D$	dv/dt	15	V/ns
Operation and storage temperature	$T_{stg}, T_j$	-55 to 150	$^\circ\text{C}$

## ■ Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal resistance, junction-case	$R_{\theta JC}$	1.5	$^{\circ}\text{C}/\text{W}$
Thermal resistance, junction-ambient <sup>4)</sup>	$R_{\theta JA}$	62	$^{\circ}\text{C}/\text{W}$

## ■ Electrical Characteristics at $T_j=25^{\circ}\text{C}$ unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Drain-source breakdown voltage	$BV_{DSS}$	900			V	$V_{GS}=0\text{ V}, I_D=250\ \mu\text{A}$
		960	1070			$V_{GS}=0\text{ V}, I_D=250\ \mu\text{A}, T_j=150^{\circ}\text{C}$
Gate threshold voltage	$V_{GS(th)}$	2.0		4.0	V	$V_{DS}=V_{GS}, I_D=250\ \mu\text{A}$
Drain-source on-state resistance	$R_{DS(on)}$		1.0	1.2	$\Omega$	$V_{GS}=10\text{ V}, I_D=2\text{ A}$
			2.88			$V_{GS}=10\text{ V}, I_D=2\text{ A}, T_j=150^{\circ}\text{C}$
Gate-source leakage current	$I_{GSS}$			100	nA	$V_{GS}=30\text{ V}$
				-100		$V_{GS}=-30\text{ V}$
Drain-source leakage current	$I_{DSS}$			10	$\mu\text{A}$	$V_{DS}=900\text{ V}, V_{GS}=0\text{ V}$

## ■ Dynamic Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Input capacitance	$C_{iss}$		743.12		pF	$V_{GS}=0\text{ V}, V_{DS}=50\text{ V}, f=100\text{ kHz}$
Output capacitance	$C_{oss}$		36.22		pF	
Reverse transfer capacitance	$C_{rss}$		1.31		pF	
Turn-on delay time	$t_{d(on)}$		33.23		ns	$V_{GS}=10\text{ V}, V_{DS}=400\text{ V}, R_G=33\ \Omega, I_D=5\text{ A}$
Rise time	$t_r$		26.50		ns	
Turn-off delay time	$t_{d(off)}$		44.00		ns	
Fall time	$t_f$		17.63		ns	

## ■ Gate Charge Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Total gate charge	$Q_g$		12.50		nC	$I_D=5\text{ A}$ , $V_{DS}=400\text{ V}$ , $V_{GS}=10\text{ V}$
Gate-source charge	$Q_{gs}$		3.75		nC	
Gate-drain charge	$Q_{gd}$		4.28		nC	
Gate plateau voltage	$V_{\text{plateau}}$		5.8		V	

## ■ Body Diode Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Diode forward current	$I_S$			5	A	$V_{GS} < V_{th}$
Pulsed source current	$I_{SP}$			15		
Diode forward voltage	$V_{SD}$			1.3	V	$I_S=5\text{ A}$ , $V_{GS}=0\text{ V}$
Reverse recovery time	$t_{rr}$		265.87		ns	$V_R=400\text{ V}$ , $I_S=5\text{ A}$ , $di/dt=100\text{ A}/\mu\text{s}$
Reverse recovery charge	$Q_{rr}$		2.88		$\mu\text{C}$	
Peak reverse recovery current	$I_{rrm}$		19.51		A	

## ■ Note

- 1) Calculated continuous current based on maximum allowable junction temperature.
- 2) Repetitive rating; pulse width limited by max. junction temperature.
- 3)  $P_d$  is based on max. junction temperature, using junction-case thermal resistance.
- 4) The value of  $R_{\theta JA}$  is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with  $T_a=25\text{ }^\circ\text{C}$ .
- 5)  $V_{DD}=100\text{ V}$ ,  $R_G=47\text{ }\Omega$ ,  $L=10\text{ mH}$ , starting  $T_j=25\text{ }^\circ\text{C}$ .

■ **Electrical Characteristics Diagrams**

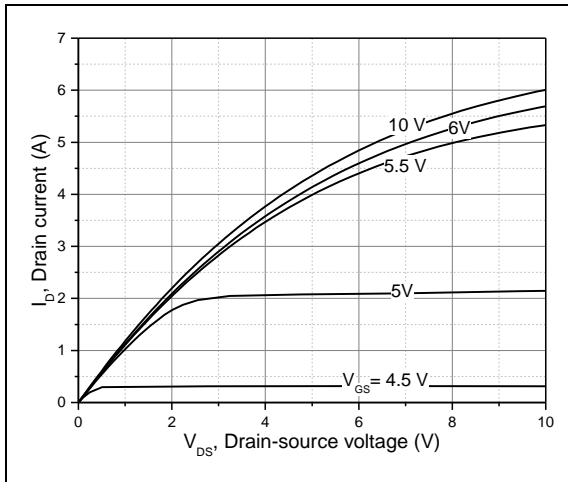


Figure 1, Typ. output characteristics

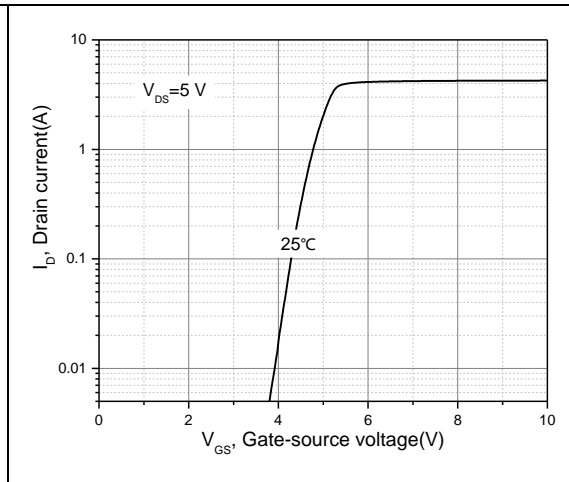


Figure 2, Typ. transfer characteristics

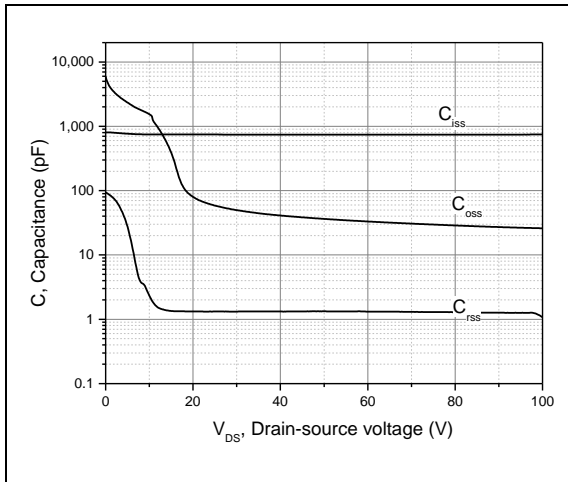


Figure 3, Typ. capacitances

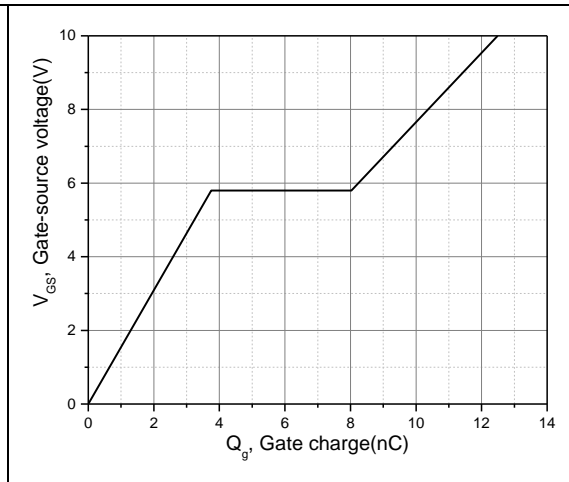


Figure 4, Typ. gate charge

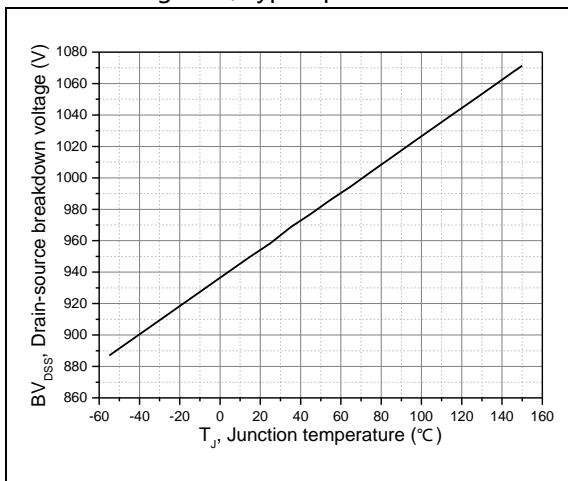


Figure 5, Drain-source breakdown voltage

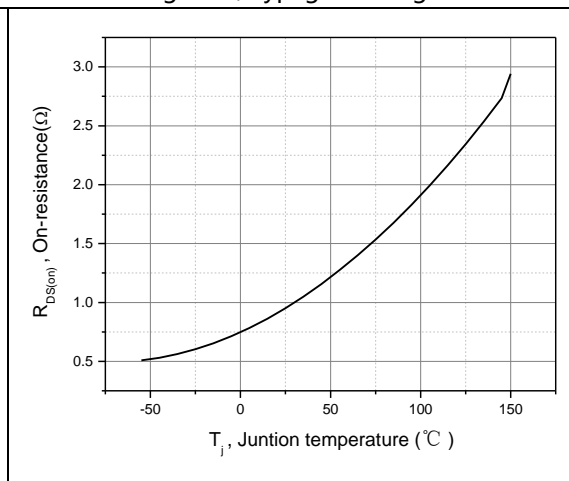


Figure 6, Drain-source on-state resistance

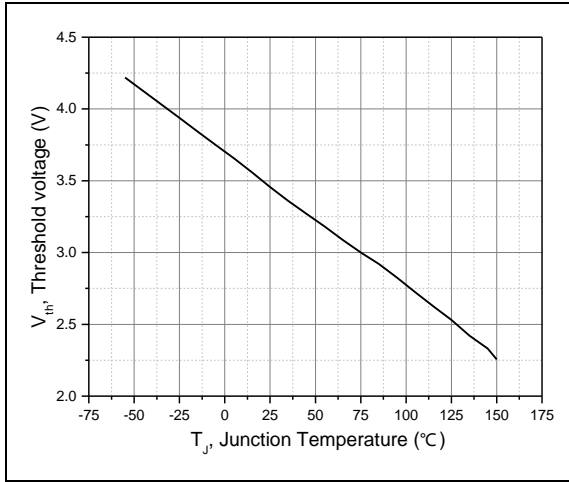


Figure 7, Threshold voltage

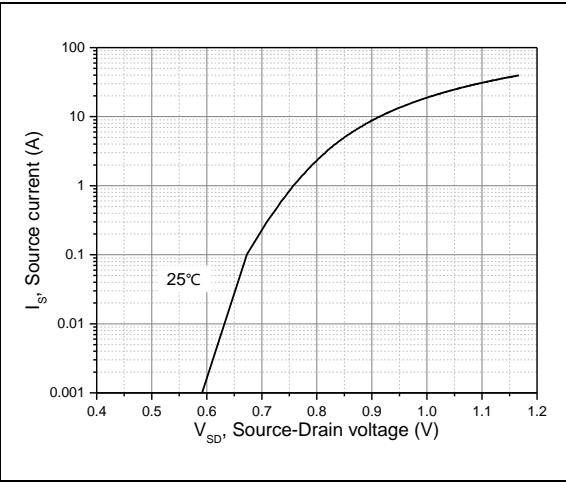


Figure 8, Forward characteristic of body diode

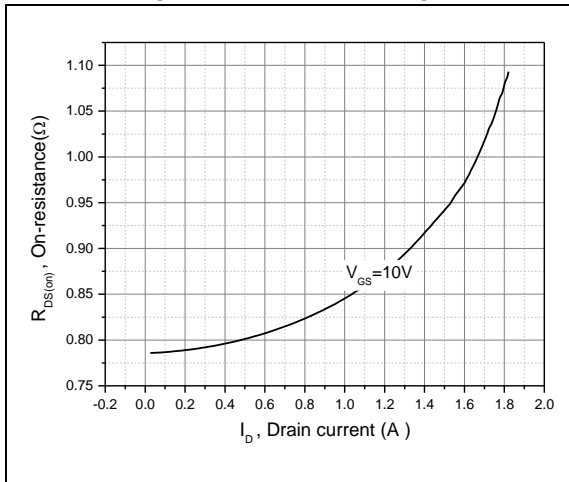


Figure 9, Drain-source on-state resistance

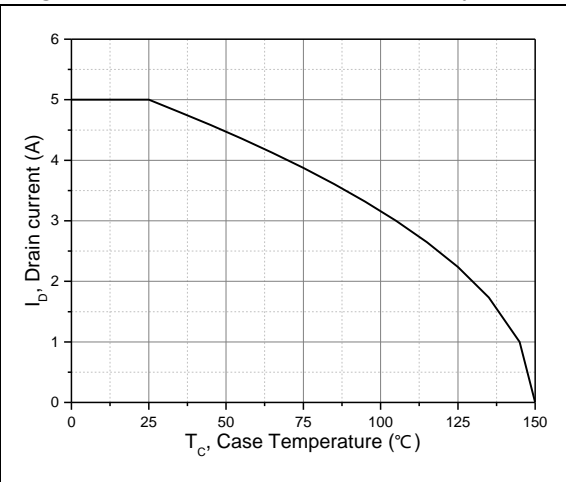


Figure 10, Drain current

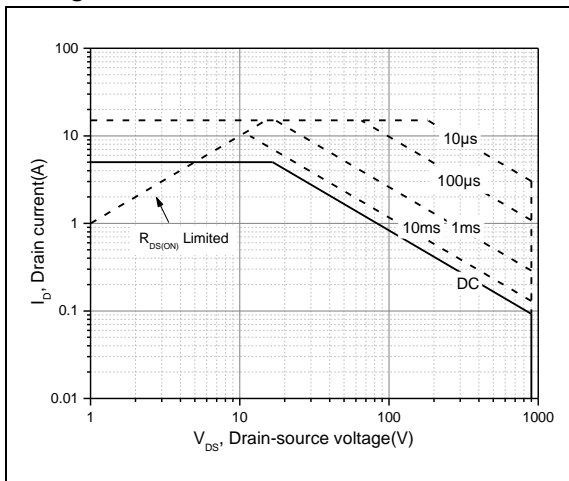


Figure 11, Safe operation area for TO251/TO262 TC=25 °C

■ Test circuits and waveforms

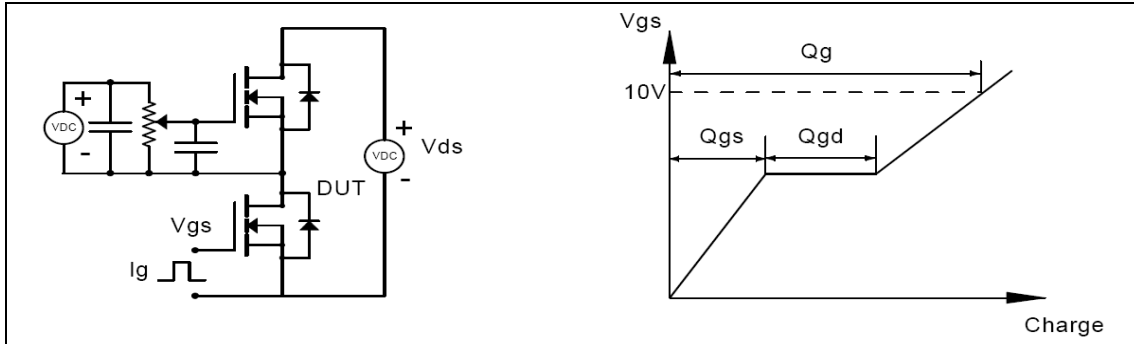


Figure 1, Gate charge test circuit & waveform

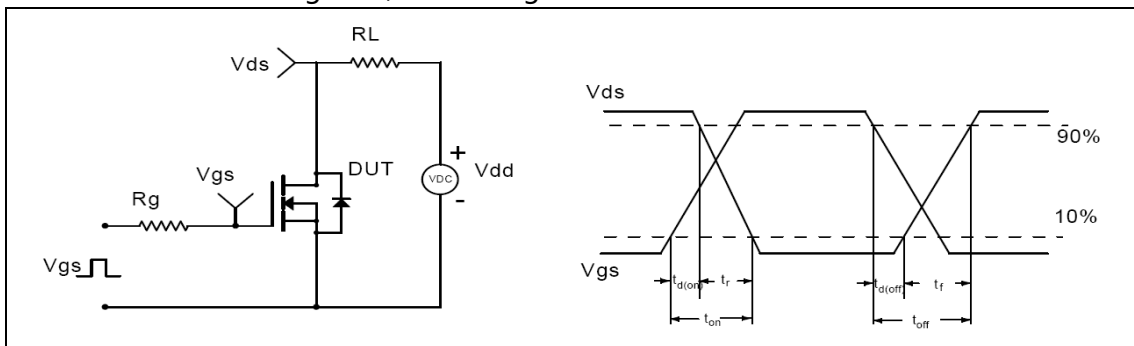


Figure 2, Switching time test circuit & waveforms

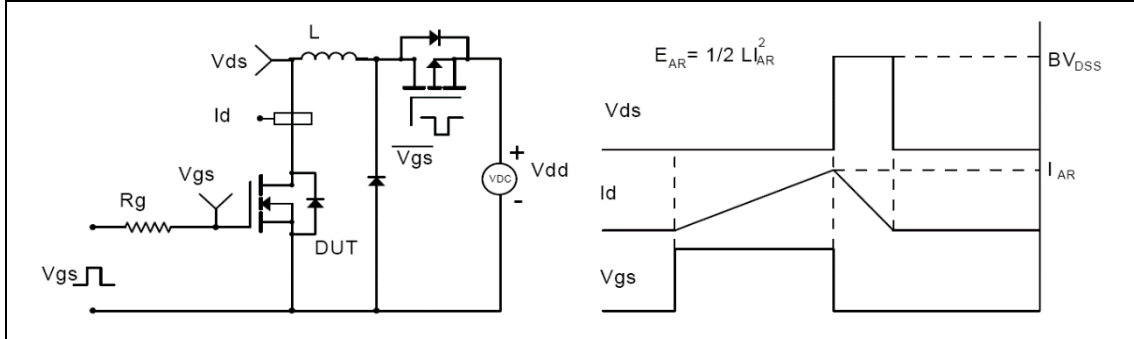


Figure 3, Unclamped inductive switching (UIS) test circuit & waveforms

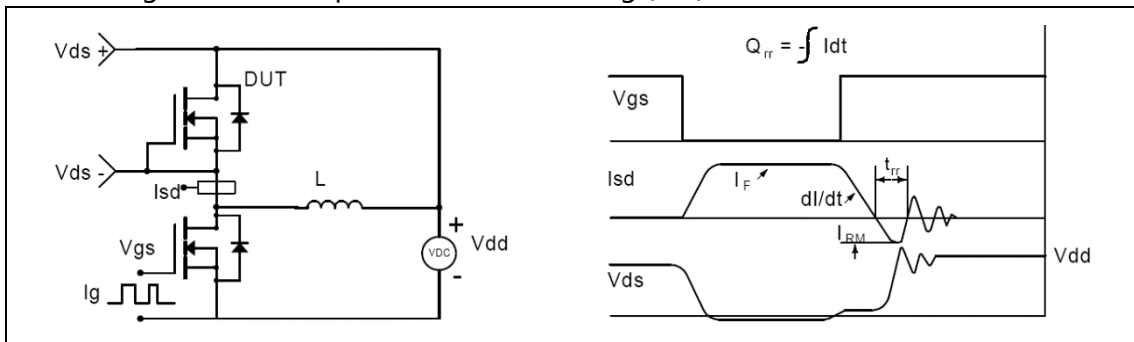
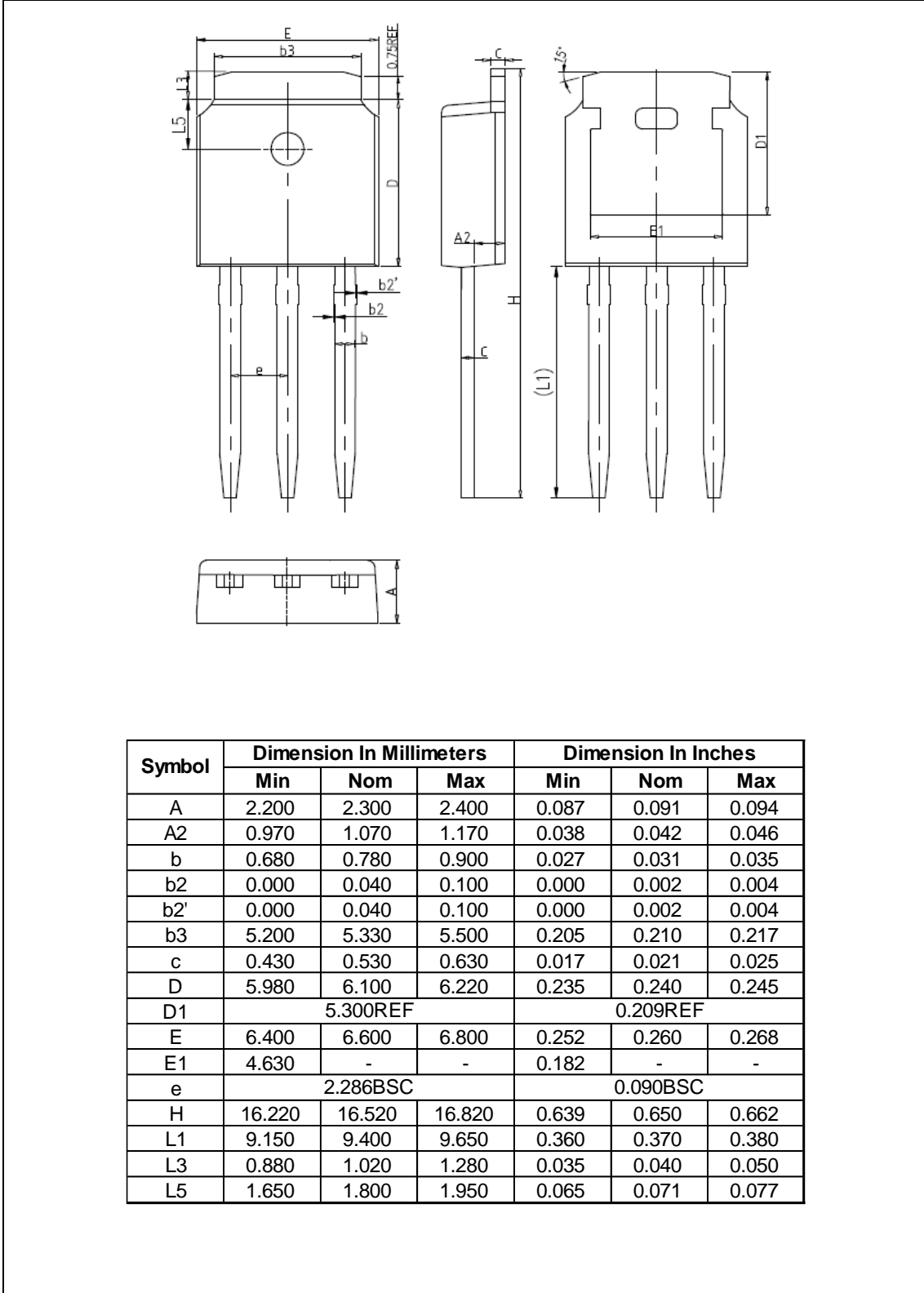


Figure 4, Diode reverse recovery test circuit & waveforms

**■ Package Information**

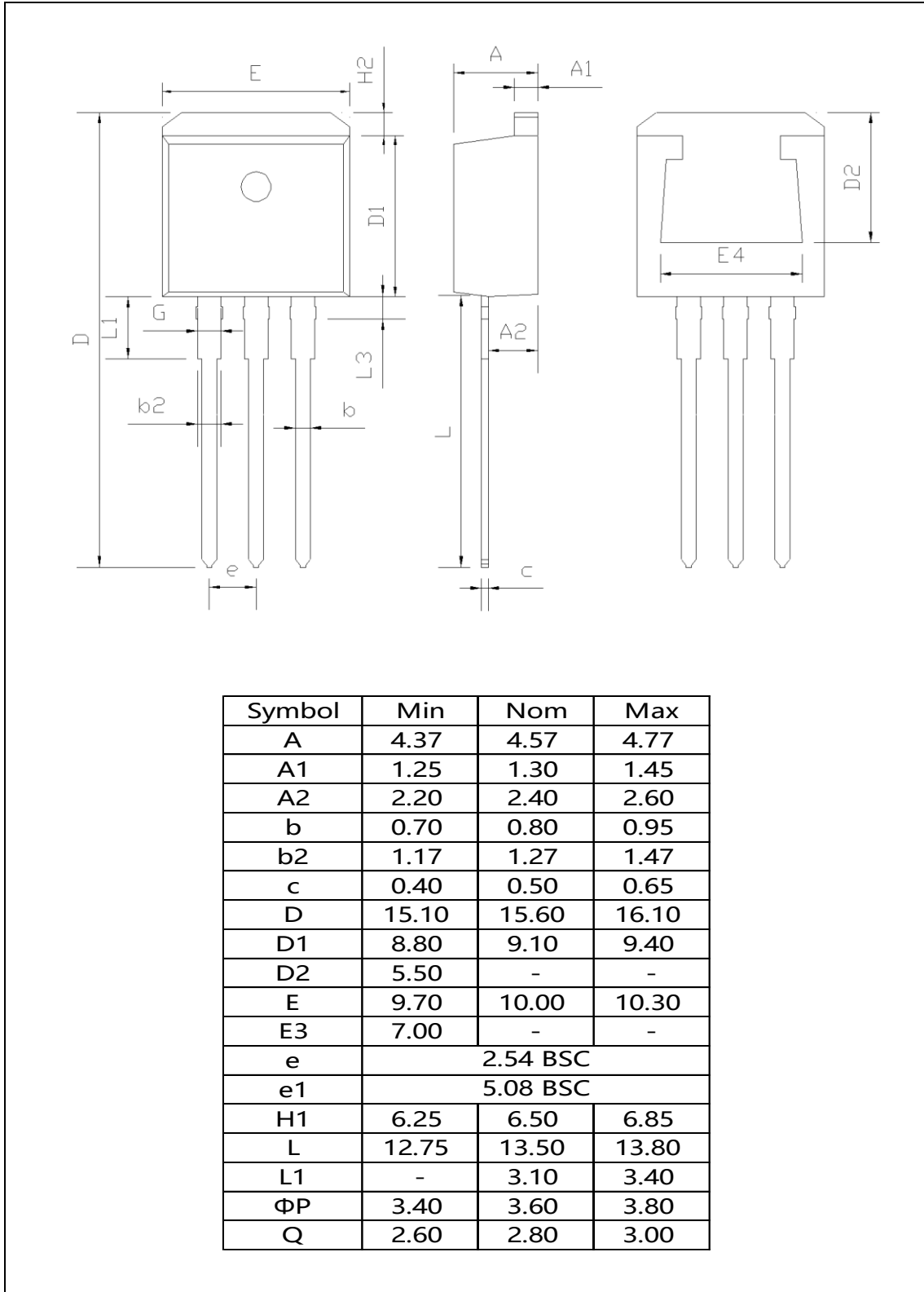
Figure1, TO251 package outline dimension





**■ Package Information**

Figure2, TO262 package outline dimension



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**■ Ordering Information**

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Package	Units/Tube	Tubes/Inner Box	Units/Inner Box	Inner Box/Carton Box	Units/Carton Box
TO251	75	66	4950	6	29700
TO262	50	20	1000	6	6000

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**■ Product Information**

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Product	Package	Pb Free	RoHS	Halogen Free
OSG90R1K2AF	TO251	yes	yes	yes
OSG90R1K2IF	TO262	yes	yes	yes